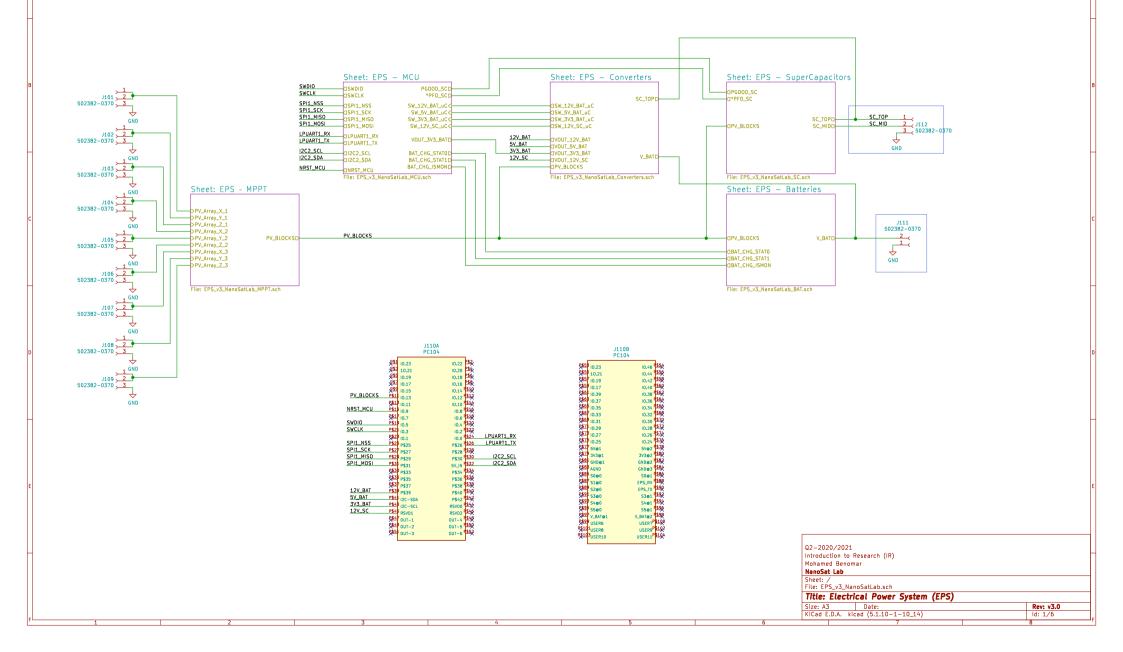
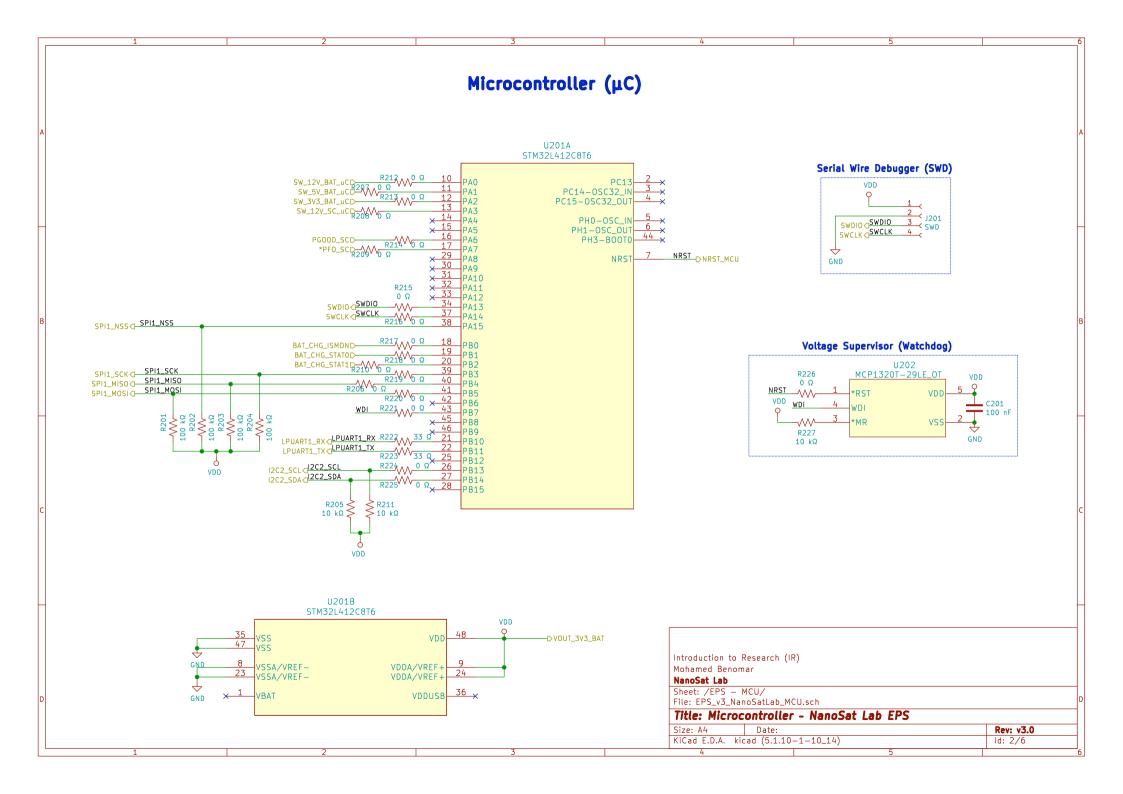
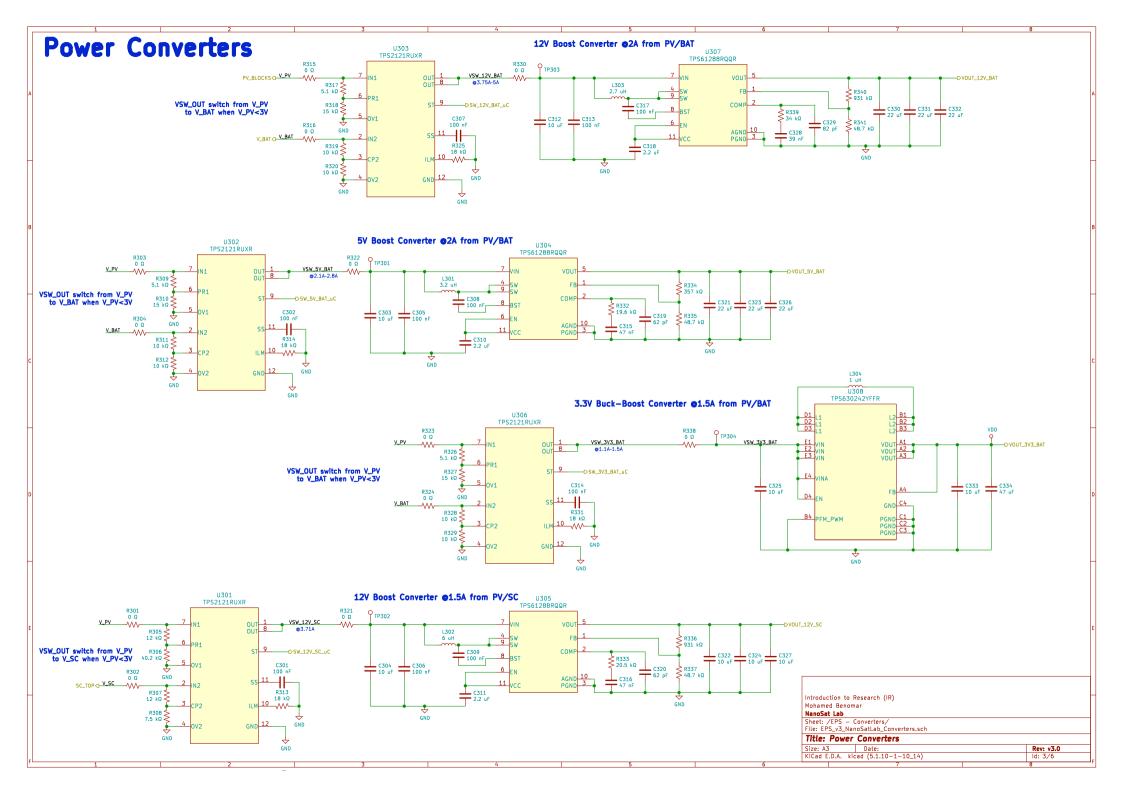
## Electrical Power System (EPS) SuperCapacitors v3.0







## SuperCapacitor Charger L401 3.3 uH U401 LTC3128 R407 TP402 0 Ω R401 0 Ω PV\_BLOCKS ( \_\_\_\_\_ / \_\_\_ / \_\_\_\_ VIN VOUT -VVV-DSC\_TOP 20 C403 C404 VOUTP Ceramic and close to VCC and GND 10 uF 10 uF Short trace VOUTS MLCC X7R or X7S >10μF R405 2.21 MΩ 18 SC\_MID GND GND GND R404 8 15 MAXV 0 Ω Large Values PGOOD\_SC Close to R403the pin $142 \text{ k}\Omega$ \*PFO\_SC 13 Pulls low when YOUT is less than 96.75% R406 301 kΩ Short and wide a trace 5 10 × 22 × 6 RSENS $\begin{array}{c|c} & C402 & R402 \\ \hline & 470 & pF & 3.57 & k\Omega \end{array}$ C405 GND Introduction to Research (IR) Mohamed Benomar NanoSat Lab Sheet: /EPS - SuperCapacitors/ File: EPS\_v3\_NanoSatLab\_SC.sch Title: SuperCapacitors Charger Size: A4 Date: Rev: v3.0 KiCad E.D.A. kicad (5.1.10-1-10\_14) ld: 4/6

## **Battery Charger** Prevent battery discharge when the input voltage is below the battery voltage and for MPPT low RDS(ON) and breakdown voltage to stand off maximum supply voltage. Q501 R501 Q <sub>TP501</sub> INFET 0 Ω low-ESR PV\_BLOCKS (I—VVV-C503 C505 C506 A maximum 4.7µF high quality ceramic capacitor $C_{BST} > 50 \cdot \frac{Q_{GH}}{V} = 10 \cdot Q_{GH}$ is recommended. U501 C507 GND $V_{GS}$ 0.22 uF 0.1 uF The rated drain current for $V_{IN} \bullet V_{BAT} - V_{BAT}^2$ both MOSFETs must be I<sub>LMAX</sub> = I<sub>CHGMAX</sub> + greater than the maximum 2 • f<sub>SW</sub> • L • V<sub>IN</sub> R502 1.5 MΩ GND inductor current. Peak inductor Q502 T\_NMOS current is approximately: $R_{EN2} = R_{EN1} \cdot \left( \frac{V_{ENAB}}{1.22} - 1 \right)$ ENAB R503 ≤ Q503 B\_NMOS BG +L501 |pp\_ripple = 30% · ICHGMAX D501 C509 1A 10 uF GND Saturation current for the $C > 4.7 \mu F$ $L = \frac{V_{\text{IN}} \cdot V_{\text{BAT}}}{0.3 \cdot f_{\text{SW}} \cdot I_{\text{CHGMAX}} \cdot V_{\text{IN}}}$ inductor to be at least 20% ceramic INTVCC | higher than the maximum MPPT disabled INTVCC close charge current. <20mΩ INTVCC PGND - GND MODE2 SENSE R509 RSENSE = 50mV/R\_SENSE 22 mΩ reverse voltage greater than the input supply voltage maximum ISMON = 20 \* (V\_SENSE - V\_VAT) BAT\_CHG\_ISMON C **-**V\_BAT ISMON BAT TP502 R507 \$ R510 0 Ω BAT\_CHG\_STATO <-VFB = VBAT/217 INTVCC R508 L NΩ 8 BAT\_CHG\_STAT1 <-STAT1 RSENSE R506 C504 3.36 kΩ 0.01 uF LTC4013EUFD-PBF $R_T [K\Omega] = 40.2 / f_SW^1.088 [MHz]_{504}$ 86.6 k $\Omega$ ₹ R505 75 kΩ GND TO SENSE TO SENSE TO BAT Low Battery Volatge Fault 4013 F18 GND GND $R_LB [\Omega] = V_LB / 20uA$ $V_LB = 3V/2 -> R_LB = 75 k\Omega$ Figure 17. Sense Resistor PCB Layout Introduction to Research (IR) Mohamed Benomar NanoSat Lab Sheet: /EPS - Batteries/ File: EPS\_v3\_NanoSatLab\_BAT.sch Title: Battery Charger Size: A4 Date: Rev: v3.0 KiCad E.D.A. kicad (5.1.10-1-10\_14) ld: 5/6

## MPPT Converters and PV Cells

